

1N6792
1N6792R

45 Volts
25 Amps

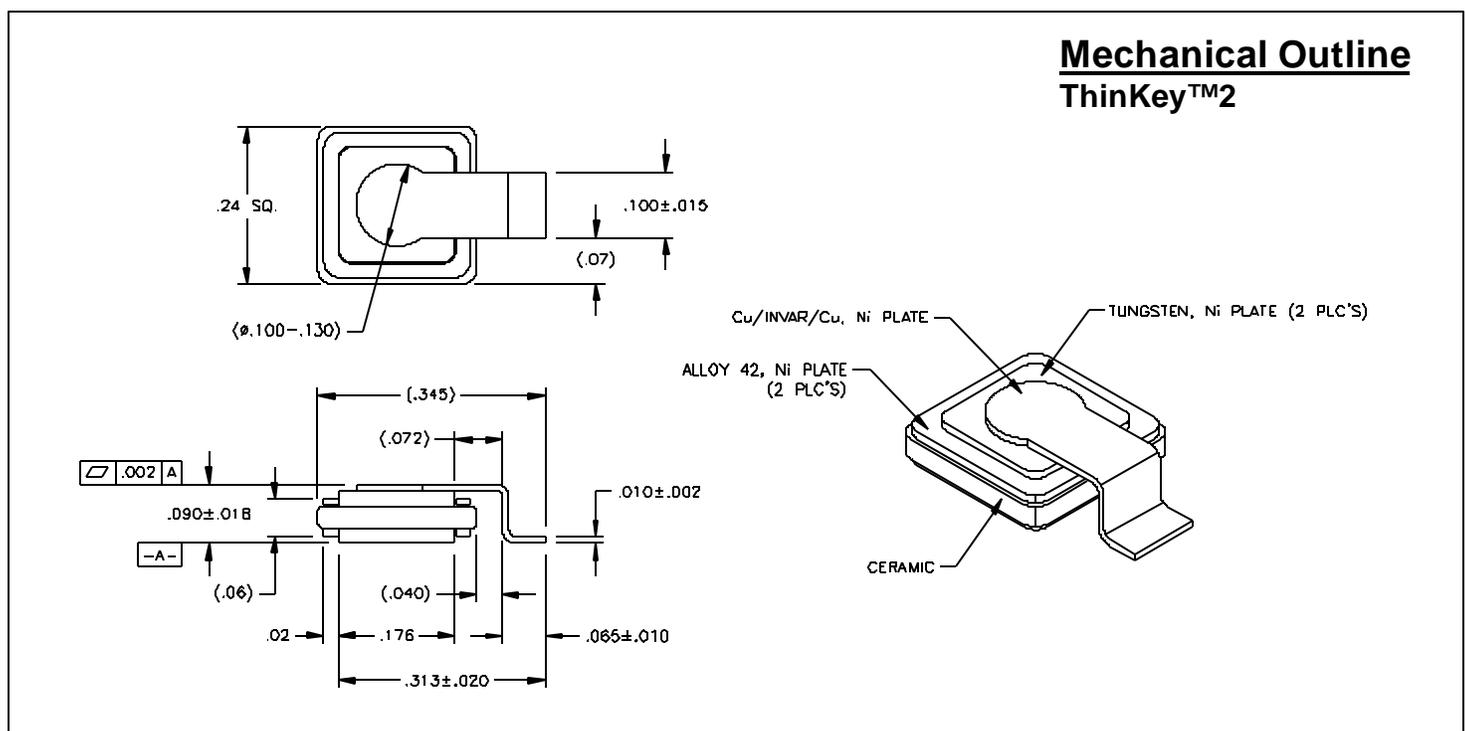
LOW VOLTAGE
DROP SCHOTTKY
DIODE

Features

- Tungsten/Platinum schottky barrier for very low VF
- Oxide passivated structure for very low leakage currents
- Guard ring protection for increased reverse energy capability
- Epitaxial structure minimizes forward voltage drop
- Hermetically sealed, low profile ceramic surface mount power package
- Low package inductance
- Very low thermal resistance
- Available as standard polarity (strap-to-anode, 1N6792) and reverse polarity (strap-to-cathode: 1N6792R)

Maximum Ratings @ 25°C (unless otherwise specified)

| DESCRIPTION | SYMBOL | MAX. | UNIT |
|---|-------------------|-------------|------------------------|
| Peak Repetitive Reverse Voltage | V_{RRM} | 45 | Volts |
| Working Peak Reverse Voltage | V_{RWM} | 45 | Volts |
| DC Blocking Voltage | V_R | 45 | Volts |
| Average Rectified Forward Current, $T_c \leq 145^\circ\text{C}$ | $I_{F(ave)}$ | 25 | Amps |
| derating, forward current, $T_c \geq 145^\circ\text{C}$ | di_F/dT | (3.3) | Amps/ $^\circ\text{C}$ |
| Nonrepetitive Peak Surge Current, $t_p = 8.3$ ms, half-sinewave | I_{FSM} | 125 | Amps |
| Peak Repetitive Reverse Surge Current, $t_p = 1\mu\text{s}$, $f = 1\text{kHz}$ | I_{RRM} | 2 | Amp |
| Junction Temperature Range | T_j | -65 to +175 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | -65 to +175 | $^\circ\text{C}$ |
| Thermal Resistance, Junction to Case: | θ_{JC} | 1.25 tbd | $^\circ\text{C/W}$ |
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Electrical Parameters

| DESCRIPTION | SYMBOL | CONDITIONS | MIN | TYP. | MAX | UNIT |
|---|-------------------|-----------------------|-----|------|------|------|
| Reverse (Leakage) Current | IR ₂₅ | VR= 45 Vdc, Tc= 25°C | | 300 | 1000 | μA |
| | IR ₁₂₅ | VR= 45 Vdc, Tc= 125°C | | 100 | 150 | mA |
| Forward Voltage pulse test, pw= 300 μs d/c≤ 2% | VF1 | IF= 5A, Tc= 25°C | | 375 | 475 | mV |
| | VF2 | IF= 10A, Tc= 25°C | | 430 | 520 | mV |
| | VF3 | IF= 20A, Tc= 25°C | | 510 | 610 | mV |
| | VF4 | IF= 50A, Tc= 25°C | | 740 | | mV |
| | VF5 | IF= 10A, Tc= -55°C | | 480 | 580 | mV |
| | VF6 | IF= 10A, Tc= 125°C | | 360 | | mV |
| Junction Capacitance | Cj1 | VR= 10 Vdc | | 525 | 600 | pF |
| | Cj2 | VR= 5 Vdc | | 725 | | pF |
| Breakdown Voltage | BVR | IR= 1 mA, Tc= 25°C | | 55 | | V |
| | | IR= 1 mA, Tc= -55°C | 45 | 50 | | V |